AMENDMENTS TO THE CLAIMS

1. (Currently Amended)A chemical mechanical polishing ~~An aqueous~~ slurry composition for the polishing of chemical-based interconnects and non-volatile memory devices which comprises:
   A. about 0.01% by weight to about 50% by weight of abrasive particles;
   B. about 0.01% to about 50% by weight of an oxidizer;
   C. at least about 500 ppm of a quaternary ammonium hydroxide for stabilizing the abrasive particles;
   D. an acid having a pKa of about 2.5 or lower in an sufficient amount to provide an acidic pH;
   E. water;
   and F. a corrosion inhibitor for copper;
   and wherein the abrasive particles comprise at least one member selected from the group consisting of silica, alumina, zirconia, titania, and ceria .

2. (Original) The composition of claim 1 wherein the amount of the abrasive particles is about 1% to about 20% by weight.

3. (Original) The composition of claim 1 wherein the amount of the abrasive particles is about 5% to about 15% by weight.

4. (Currently Amended) The composition of claim 1 wherein the abrasive particles ~~comprises~~ comprise silica particles.

5. (Original) The composition of claim 1 wherein the oxidizer comprises hydrogen peroxide.

6. (Currently Amended) The composition of claim 1 wherein the amount of oxidizer is about 0.05 ~~at~~% to about 5~~wt~~% by weight.

7. (Currently Amended) The composition of claim 1 wherein the amount of oxidizer is about 0.1~~wt~~% to about 1~~wt~~% by weight.

8. (Currently Amended) The composition of claim 1 wherein the quaternary ammonium hydroxide is represented by the formula:

~~$[N\text{-}R_4R_5R_6R_7]^- OH$~~

$[N\text{-}R_4R_5R_6R_7]^+ OH^-$

wherein each of R_4, R_5, R_6, and R_7 individually is an alkyl group of 1 to 20 carbon atoms.

9. (Original) The composition of claim 8 wherein the alkyl group contains 1 to 4 carbon atoms.

10. (Original) The composition of claim 1 wherein the quaternary ammonium hydroxide comprises tetramethyl ammonium hydroxide or tetrabutyl ammonium hydroxide.

11. (Original) The composition of claim 1 wherein the amount of quaternary ammonium hydroxide is about 1000 ppm or higher.

12. (Original) The composition of claim 1 wherein the amount of quaternary ammonium hydroxide is about 2500 ppm or higher.

13. (Original) The composition of claim 1 wherein the acid comprises phosphoric acid.

14. (Original) The composition of claim 1 wherein the pH is at least about 1.5.

15. (Original) The composition of claim 1 wherein the pH is about 1.5 to about 5.

16. (Original) The composition of claim 1 wherein the pH is at least about 2.

17. (Cancelled)

18. (Currently Amended) The composition of claim ~~16~~ 1 wherein the corrosion inhibitor comprises benzotriazole.

19. (Original) The composition of claim 1 which further comprises a surface active agent.

20. (Withdrawn) A method for polishing a metal which comprises providing on the metal an aqueous slurry composition comprising:

A. about 0.1% by weight to about 50% by weight of abrasive particles;

B. about 0.1% to about 50% by weight of an oxidizer;

C. at least about 500 ppm of a quaternary ammonium hydroxide;

D. an acid being a pKa of about 2.5 or lower in amount to provide an acidic pH;

E. and water;

and contacting the metal with a polishing pad.

21. (Withdrawn) A process for fabricating semiconductor integrated circuit structure comprising: forming circuits on the surface of a semiconductor wafer by photolithographic process; planarizing the surface by chemical mechanical polishing with the composition of claim 1.

22. (Withdrawn- Currently Amended) The process of claim 21 wherein the integrated circuit structure comprise a semiconductor substrate; a ferromagnetic metal layer; a metal selected from the group consisting of ~~group 3d~~ period 4d and 5d of the periodic table; a layer of copper or aluminum; a barrier layer; and a dielectric layer.

23. (New) The composition of claim 1 wherein the corrosion inhibitor comprises at least one member selected from the group consisting of aromatic hydroxyl compounds, acetylenic alcohols; carboxyl group containing organic compounds and anhydrides thereof, imidazoles and triazole compounds.

24. (New) The composition of claim 1 wherein the corrosion inhibitor comprises at least one member selected from the group consisting of benzotriazole, 1, 2, 4-triazole o-

tolyltriazole, m-tolyltriazole, p-tolyltriazole, carboxybenzotriazole, 1-hydroxybenzotriazole, nitrobenzotriazole and dihydroxypropylbenzotriazole.

25. (New) The composition of claim 13 wherein the amount of phosphoric acid is about 0.05% to about 5% by weight.

26. (New) The composition of claim 1 which further comprises acids having pKa greater than 2.5 in composition with the acids having a pKa of less than 2.5.

27. (New) The composition of claim 1 wherein the amount of corrosion inhibitor is about 0.01% to about 1.5% by weight.

28. (New) The composition of claim 19 wherein the amount of surface active agent is about 0.1 ml/l to about 100ml/l.

29. (New) The composition of claim 1 wherein the quaternary ammonium hydroxide is at least one member selected from the group consisting of tetramethylammonium hydroxide, tetraethylammonium hydroxide, tetrapropylammonium hydroxide, tetrabutylammonium hydroxide, ethyltrimethylammonium hydroxide, diethyldimethylammonium hydroxide and benzyltrimethylammonium hydroxide.